Alireza Kashir

List of Publications by Year
in descending order

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20 papers	399 citations	840776 11 h-index	752698 20 g-index
20 all docs	20 docs citations	20 times ranked	242 citing authors

#	Article	IF	Citations
1	Large Remnant Polarization in a Wake-Up Free Hf_{0.5}Zr_{0.5}O₂ Ferroelectric Film through Bulk and Interface Engineering. ACS Applied Electronic Materials, 2021, 3, 629-638.	4.3	79
2	Hafnium Oxide (HfO₂) â€“ A Multifunctional Oxide: A Review on the Prospect and Challenges of Hafnium Oxide in Resistive Switching and Ferroelectric Memories. Small, 2022, 18, e2107575.	10.0	78
3	Defect Engineering to Achieve Wakeâ€up Free HfO₂â€Based Ferroelectrics. Advanced Engineering Materials, 2021, 23, .	3.5	53
4	Effect of dead layers on the ferroelectric property of ultrathin HfZrOx film. Applied Physics Letters, 2020, 117, .	3.3	37
5	A new approach to achieving strong ferroelectric properties in TiN/Hf_{0.5}Zr_{0.5}O₂/TiN devices. Nanotechnology, 2021, 32, 055703.	2.6	21
6	High polarization and wake-up free ferroelectric characteristics in ultrathin Hf_{0.5}Zr_{0.5}O₂ devices by control of oxygen-deficient layer. Nanotechnology, 2022, 33, 085206.	2.6	21
7	Towards an ideal high-Îº HfO₂â€“ZrO₂-based dielectric. Nanoscale, 2021, 13, 13631-13640.	5.6	18
8	Ferroelectric and Dielectric Properties of Hf_{0.5}Zr_{0.5}O₂ Thin Film Near Morphotropic Phase Boundary. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000819.	1.8	18
9	A CMOS-compatible morphotropic phase boundary. Nanotechnology, 2021, 32, 445706.	2.6	12
10	Hf_{1â€“x}Zr_xO₂/ZrO₂ Nanolaminate Thin Films as a High-Îº Dielectric. ACS Applied Electronic Materials, 2021, 3, 5632-5640.	4.3	12
11	Dielectric Properties of Strained Nickel Oxide Thin Films. Journal of the Korean Physical Society, 2019, 74, 984-988.	0.7	11
12	Effects of high pressure oxygen annealing on Hf_{0.5}Zr_{0.5}O₂ ferroelectric device. Nanotechnology, 2021, 32, 315712.	2.6	11
13	A thin film perspective on quantum functional oxides. Current Applied Physics, 2019, 19, 207-214.	2.4	6
14	A grease for domain walls motion in HfO₂-based ferroelectrics. Nanotechnology, 2022, 33, 155703.	2.6	6
15	Strain-Induced Increase of Dielectric Constant in EuO Thin Film. Materials Research Express, 2019, 6, 106321.	1.6	5
16	Pulsed Laser Deposition of Rocksalt Magnetic Binary Oxides. Thin Solid Films, 2019, 692, 137606.	1.8	5
17	Strain effect on magnetic-exchange-induced phonon splitting in NiO films. Journal of Physics Condensed Matter, 2020, 32, 405607.	1.8	2
18	Improvement of endurance and switching speed in Hf_{1â^'x}Zr _x O₂ thin films using a nanolaminate structure. Nanotechnology, 2022, 33, 395205.	2.6	2

#	Article	IF	Citations
19	Spin-phonon interaction increased by compressive strain in antiferromagnetic MnO thin films. Journal of Physics Condensed Matter, 2020, 32, 175402.	1.8	1
20	Two-step deposition of TiN capping electrodes to prevent degradation of ferroelectric properties in an in-situ crystallized TiN/Hf_{0.5}Zr_{0.5}O₂/TiN device. Nano Express, 2022, 3, 015004.	2.4	1